

HIGH-SPEED 3.3V 32K x 8 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

PRELIMINARY IDT70V9079S/L

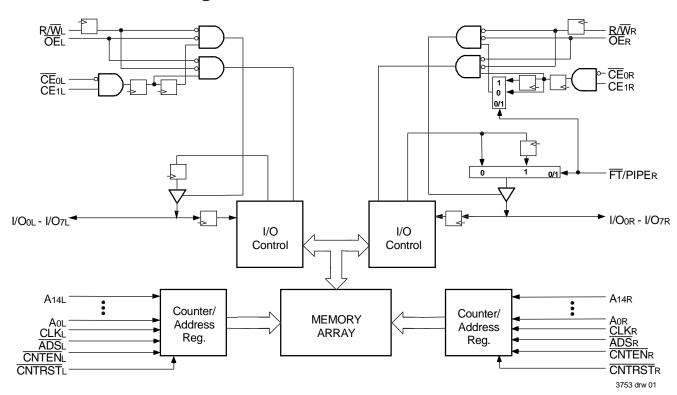
Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 9/12/15ns (max.)
- Low-power operation
 - IDT70V9079S
 - Active: 429mW (typ.)
 - Standby: 3.3mW (typ.)
 - IDT70V9079L
 - Active: 429mW (typ.)
 - Standby: 1.32mW (typ.)
- ◆ Flow-Through or Pipelined output mode on Right Port via the FT/PIPER pin
- Counter enable and reset features
- Dual chip enables allow for depth expansion without

additional logic

- Full synchronous operation on both ports
 - 4ns setup to clock and 1ns hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 9ns clock to data out in the Pipelined output mode
 - Self-timed write allows fast cycle time
 - 15ns cycle time, 66MHz operation in the Pipelined output mode
- Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- LVTTL- compatible, single 3.3V (±0.3V) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 100 pin Thin Quad Flatpack (TQFP)

Functional Block Diagram



JUNE 1999

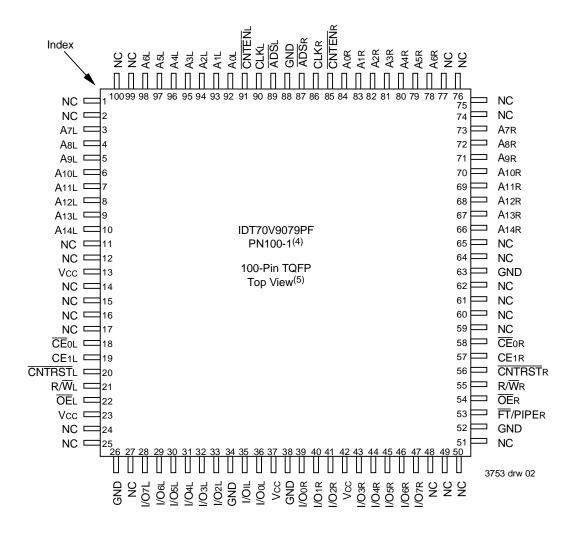
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Description:

The IDT70V9079 is a high-speed $32K \times 8$ bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times.

With an input data register, the IDT70V9079 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by CE0 and CE1, permits the on-chip circuitry of each port to enter a very LOW standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 429mW of power.

Pin Configurations (1,2,3)



- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names
Œ0L, CE1L	Œ0R, CE1R	Chip Enables
$R/\overline{W}L$	R/W̄R	Read/Write Enable
ŌĒL	OE R	Output Enable
A0L - A14L	A0R - A14R	Address
I/O0L - I/O7L	I/Oor - I/O7R	Data Input/Output
CLKL	CLKR	Clock
AD S L	AD SR	Address Strobe
CNTENL	<u>CNTEN</u> R	Counter Enable
CNTRSTL	<u>CNTRST</u> R	Counter Reset
— FT/PIPER		Flow-Through/Pipeline
V	CC	Power
Gl	ND	Ground

3753 tbl 01

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	Œ₀	CE ₁	R/W	I/O0-7	Mode
Х	\uparrow	Н	Х	Χ	High-Z	Deselected
Х	\uparrow	Χ	L	Χ	High-Z	Deselected
Х	1	L	Н	L	DATAIN	Write
L	1	L	Н	Н	DATAout	Read
Н	Χ	L	Н	Χ	High-Z	Outputs Disabled

NOTES:

1. "H" = V_{IH} , "L" = V_{IL} , "X" = Don't Care. 2. \overline{ADS} , \overline{CNTEN} , \overline{CNTRST} = X.

3. $\overline{\text{OE}}$ is an asynchronous input signal.

3753 tbl 02

Truth Table II—Address Counter Control(1,2)

Address	Previous Address	CLK	ĀDS	CNTEN	CNTRST	I/O ⁽³⁾	Mode
Х	Х	1	Н	Н	L	DATA (0)	Counter Reset to Address 0
An	Х	1	L ⁽⁴⁾	Н	Н	DATA VO(n)	External Address Utilized
Х	An	1	Н	Н	Н	DATA (O(n)	External Address Blocked—Counter Disabled
Х	An	1	Н	L ⁽⁵⁾	Н	DATA //O(n+1)	Counter Enable—Internal Address Generation

- 1. "H" = V_{IH}, "L" = V_{IL}, "X" = Don't Care.
- 2. \overline{CE}_0 and \overline{OE} = VIL; CE1 and R/ \overline{W} = VIH.
- 3. Outputs configured in Flow-Through Output mode; if outputs are in Pipelined mode the data out will be delayed by one cycle.
- 4. \overline{ADS} is independent of all other signals including \overline{CE}_0 and CE_1 .
- 5. The address counter advances if $\overline{\text{CNTEN}} = \text{Vil.}$ on the rising edge of CLK, regardless of all other signals including $\overline{\text{CE}}_0$ and CE1.

Temperature and Supply Voltage(1,2)

Grade	Ambient Temperature	GND	Vcc		
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V		
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V		

NOTES:

1. This is the parameter TA. 2. Industrial temperature: for specific speeds, packages and powers contact your sales office.

Recommend DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	3.0	3.3	3.6	٧
GND	Ground	0	0	0	٧
VIH	Input High Voltage	2.2	_	Vcc + 0.3V ⁽²⁾	٧
VIL	Input Low Voltage	-0.3 ⁽²⁾		0.8	V

3753 tbl 05

NOTES:

3753 tbl 04

- 1. VTERM must not exceed Vcc +0.3V.
- 2. $V_{IL} \ge -1.5V$ for pulse width less than 10ns.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-55 to +125	°C
ЮИТ	DC Output Current	50	mA

3753 tbl 06

NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc +0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20 mA for the period of VTERM $\geq Vcc + 0.3V$.

Capacitance ($T_A = +25^{\circ}C$, f = 1.0 MHz)

Symbol	Parameter ⁽¹⁾	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	9	pF
Соит ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF

3753 tbl 07

- 1. These parameters are determined by device characterization, but are not production tested.
- 2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references Ci/o.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 3.3V ± 0.3V)

			70V9079S		70V9		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	Vcc = 3.3V, V _{IN} = 0V to Vcc		10	1	5	μA
llo	Output Leakage Current	CE0 = VIH or CE1 = VIL, VOUT = 0V to VCC	ı	10	ı	5	μΑ
Vol	Output Low Voltage	loL = +4mA	_	0.4	-	0.4	V
Voh	Output High Voltage	IOH = -4mA	2.4	_	2.4	_	٧

NOTE:

3753 tbl 08

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(6,7)}$ (Vcc = 3.3V ± 0.3V)

						79X9 Only	70V90 Com'l		70V90 Com'l		
Symbol	Parameter	Test Condition	Versi	on	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	CEL and CER = VIL Outputs Open f = fMAX ⁽¹⁾	COM'L	S L	180 180	260 225	150 150	240 205	130 130	220 185	mA
	(Doil 1 of a Active)	I - IMAX	IND	S L							
ISB1	Standby Current (Both Ports - TTL Level Inputs)	\overline{CE} L and \overline{CE} R = VIH f = fMAX ⁽¹⁾	COM'L	S L	50 50	75 65	40 40	65 50	30 30	55 35	mA
	Level inputs)		IND	S L	11		-				
ISB2	Standby Current (One Port - TTL Level Inputs)	CEA" = VIL and CEB" = VIH ⁽³⁾ Active Port Outputs Open, f=fMAX ⁽¹⁾	COM'L	S L	110 110	170 150	100 100	160 140	90 90	150 130	mA
	Level inputs)		IND	S L			-				
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	Both Ports CER and CEL ≥ Vcc - 0.2V Vn ≥ Vcc - 0.2V or	COM'L	S L	1.0 0.4	5 3	1.0 0.4	5 3	1.0 0.4	5 3	mA
	VI	$VIN \ge VCC - U.2V \text{ or } VIN \le 0.2V, f = 0^{(2)}$	IND	S L	11		-	-			
ISB4	(One Port -	$\overline{\mathbb{C}}$ A" $\leq 0.2V$ and $\overline{\mathbb{C}}$ E" $\geq V$ CC - $0.2V^{(5)}$ V N $\geq \overline{V}$ CC - $0.2V$ or V N $\leq 0.2V$, Active Port Outputs Open, f = f MaX $^{(1)}$	COM'L	S L	100 100	160 140	90 90	150 130	80 80	140 120	mA
	CMOS Level Inputs)		IND	S L					_		

NOTES:

3753 tbl 09

- 1. At f = fmAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. Vcc = 3.3V, TA = 25° C for Typ, and are not production tested. lcc pc(f=0) = 90mA (Typ).
- 5. $\overline{CE}x = V_{IL} \text{ means } \overline{CE}_{0}x = V_{IL} \text{ and } CE_{1}x = V_{IH}$
 - $\overline{CE}x = VIH \text{ means } \overline{CE}0x = VIH \text{ or } CE1x = VIL$
 - $\overline{\text{CE}}\text{x} \leq 0.2 \text{V}$ means $\overline{\text{CE}}\text{ox} \leq 0.2 \text{V}$ and $\text{CE}\text{1x} \geq \text{Vcc}$ 0.2 V
 - $\overline{CE}x \ge Vcc 0.2V$ means $\overline{CE}0x \ge Vcc 0.2V$ or $CE1x \le 0.2V$
 - 'X' represents "L" for left port or "R" for right port.
- 6. 'X' in part number indicates power rating (S or L).
- 7. Industrial temperature: for specific speeds, packages and powers contact your sales office.

^{1.} At $Vcc \le 2.0V$ input leakages are undefined.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

3753 tbl 10

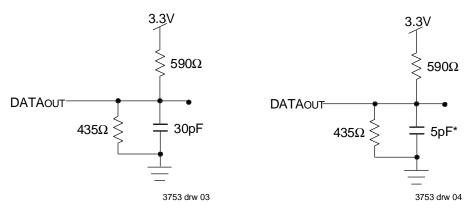


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tcklz, tckHz, tolz, and toHz).
*Including scope and jig.

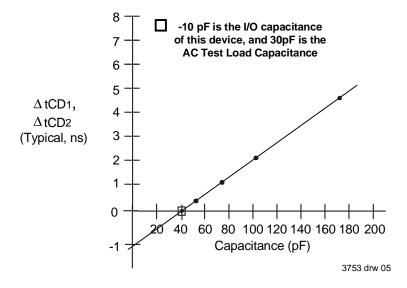


Figure 3. Typical Output Derating (Lumped Capacitive Load).

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(3,4,5)}$ (Vcc = 3.3V ± 0.3, TA = 0°C to +70°C)

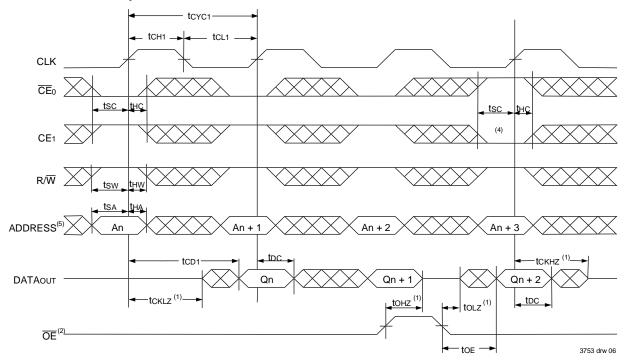
	and Write Cycle Timing)(*, *,	70V9	079X9 I Only	70V9079X12 Com'l Only		70V9079X15 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	25		30		35		ns
tCYC2	Clock Cycle Time (Pipelined) ⁽²⁾	15		20		25		ns
tCH1	Clock High Time (Flow-Through) ⁽²⁾	12		12		12		ns
ta_1	Clock Low Time (Flow-Through) ⁽²⁾	12		12		12		ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	6		8		10		ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	6		8		10		ns
tr	Clock Rise Time		3		3	_	3	ns
tr	Clock Fall Time		3		3	_	3	ns
tsa	Address Setup Time	4		4		4		ns
tha	Address Hold Time	1		1		1		ns
tsc	Chip Enable Setup Time	4		4		4		ns
thc	Chip Enable Hold Time	1		1		1		ns
tsw	R/W Setup Time	4		4		4		ns
thw	R/W Hold Time	1	_	1	_	1	_	ns
tsD	Input Data Setup Time	4		4		4		ns
thD	Input Data Hold Time	1		1		1		ns
tsad	ADS Setup Time	4		4		4		ns
thad	ADS Hold Time	1		1		1	_	ns
tscn	CNTEN Setup Time	4	_	4	_	4	_	ns
thon	CNTEN Hold Time	1	_	1	_	1	_	ns
tsrst	CNTRST Setup Time	4	_	4	_	4	_	ns
thrst	CNTRST Hold Time	1	_	1	_	1	_	ns
toe	Output Enable to Data Valid		12	_	12	_	15	ns
tOLZ	Output Enable to Output Low-Z ¹⁾	2	_	2	_	2	_	ns
tonz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽²⁾		20	_	25	_	30	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾		9		12		15	ns
toc	Data Output Hold After Clock High	2	_	2		2	_	ns
tckhz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tcklz	Clock High to Output Low-Z¹¹)	2		2		2	_	ns
Port-to-Port I	Delay	•				•	•	-
tcwdd	Write Port Clock High to Read Data Delay		35		40	_	50	ns
tocs	Clock-to-Clock Setup Time		15		15	_	20	ns

NOTES: 3753 tol 11

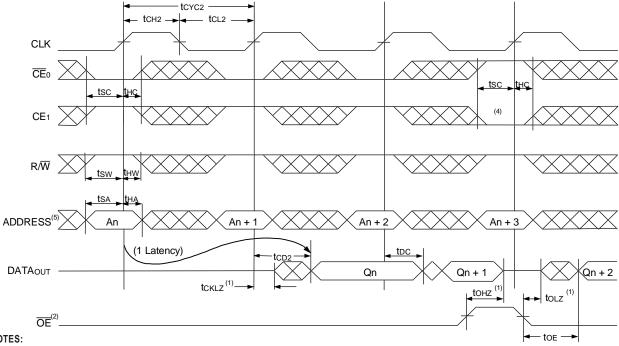
- Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
 This parameter is guaranteed by device characterization, but is not production tested.
- 2. The Pipelined output parameters (tcyc2, tcp2) always apply to the Left Port. The Right Port uses the Pipelined tcyc2 and tcp2 when FT/PIPER = VIH and the Flow-Through parameters (tcyc1, tcp1) when FT/PIPER = VIL.
- 3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (\overline{OE}) and $\overline{FT}/PIPER$. $\overline{FT}/PIPER$ should be treated as a DC signal, i.e. steady state during operation.
- 4. 'X' in part number indicates power rating (S or L).
- 5. Industrial temperature: for specific speeds, packages and powers contact your sales office.

3753 drw 07

Timing Waveform Read Cycle for Flow-Through Output on Right Port $(\overline{FT}/PIPE_R = VIL)^{(3)}$

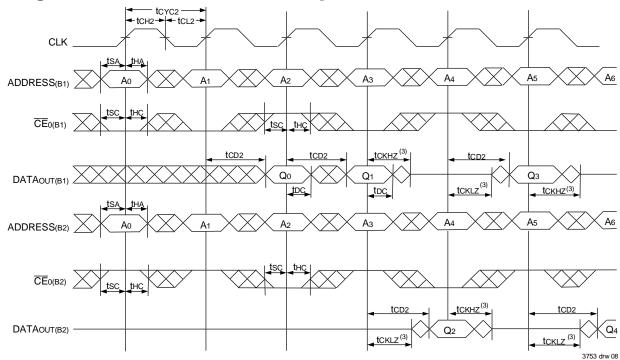


Timing Waveform of Read Cycle for Pipeline Operation (Left Port; Right Port when $\overline{FT}/PIPE_R = V_{IH})^{(3)}$

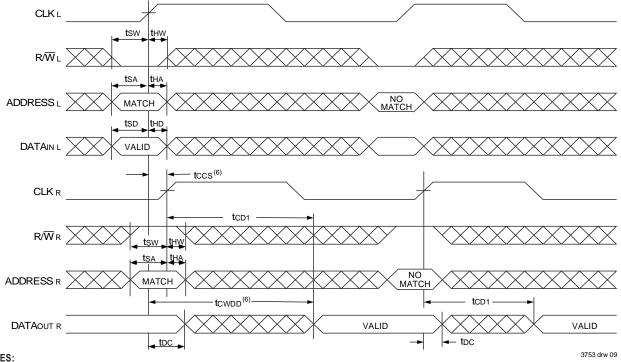


- 1. Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = V_{IL}$, \overline{CNTEN} and $\overline{CNTRST} = V_{IH}$.
- 4. The output is disabled (HIGH-impedance state) by \(\overline{CE} \) = VIH or CE1 = VIL following the next rising edge of clock. Refer to Truth Table 1.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.

Timing Waveform of a Bank Select Pipelined Read^(1,2)



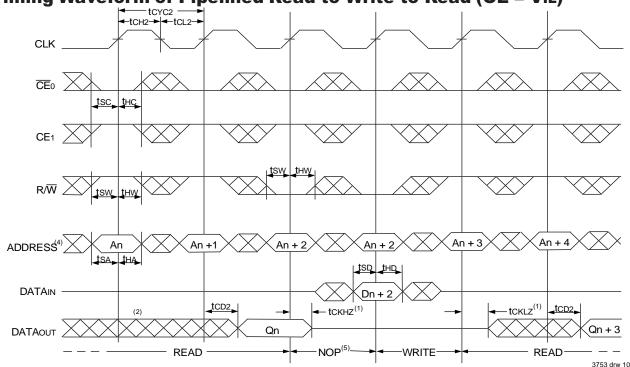
Timing Waveform of a Left Port Write of Flow-Through Right Port Read^(4,5)



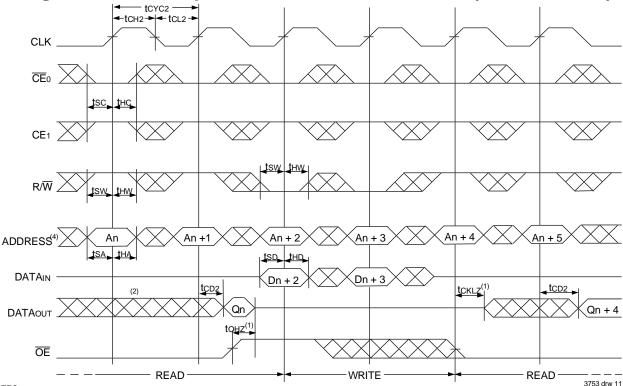
- B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9079 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{OE} and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W, \overline{CNTEN} , and \overline{CNTRST} = VIH.
- 3. Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}}$ = Vil.; CE1, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = ViH.
- 5. \overline{OE} = V_{IL} for the Right Port, which is being read from. \overline{OE} = V_{IH} for the Left Port, which is being written to.
- 6. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpb.

 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwpb does not apply in this case.

Timing Waveform of Pipelined Read-to-Write-to-Read (\overline{OE} = VIL)⁽³⁾

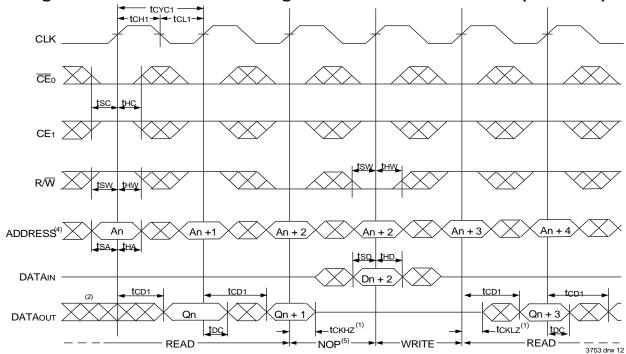


Timing Waveform of Pipelined Read-to-Write-to-Read (OE Controlled)(3)

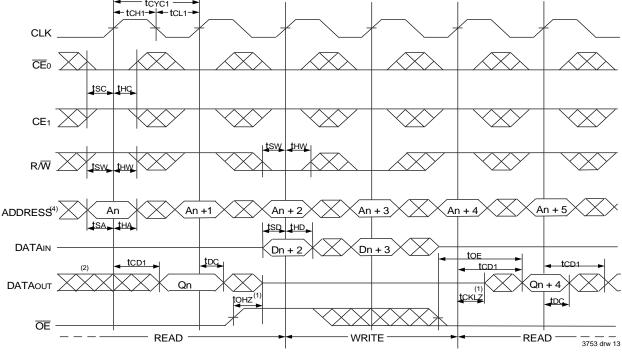


- 1. Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}}$ = V_{IL}; CE₁, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = V_{IH}.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read (OE = VIL)(3)

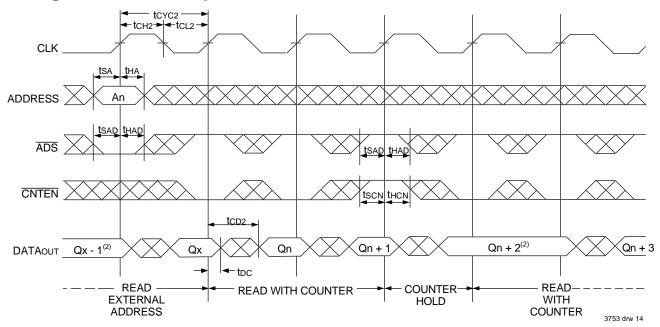


Timing Waveform of Flow-Through Read-to-Write-to-Read (OE Controlled)(3)

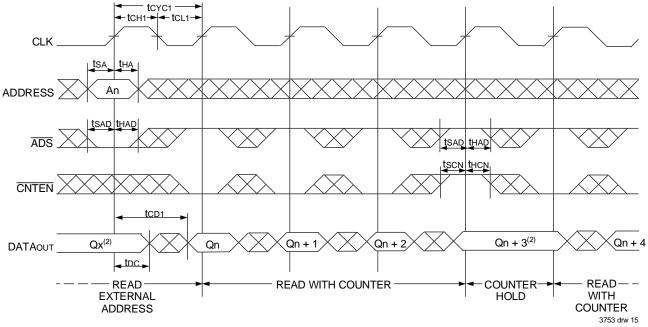


- 1. Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- $2. \ \ \, \underline{\text{Output st}\underline{\text{ate}}} \ (\text{High, Low, o\underline{r}} \ \text{High-imped}\underline{\text{ance}}) \ \text{is} \ \text{determined} \ \text{by the previous cycle control signals}.$
- 3. $\overline{\text{CE}}_0$ and $\overline{\text{ADS}}$ = ViL; CE1, $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRST}}$ = ViH.
- 4. Addresses do not have to be accessed sequentially since \overline{ADS} = V_{IL} constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



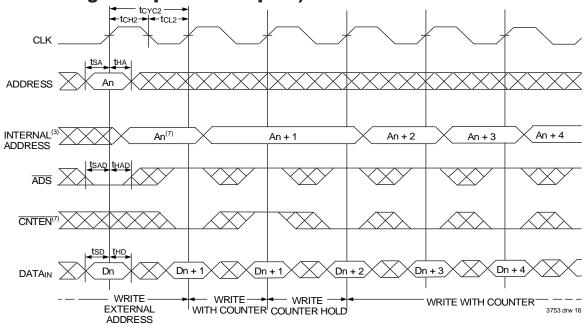
Timing Waveform of Flow-Through Counter Read with Address Counter Advance⁽¹⁾



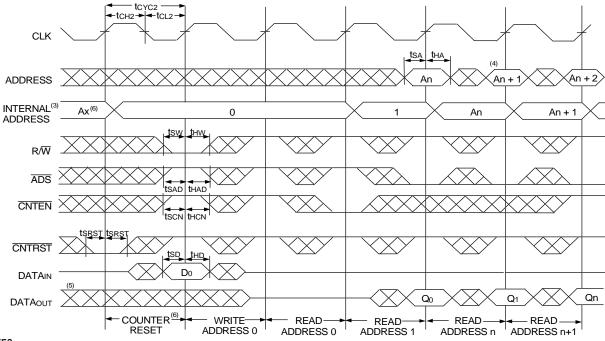
- 1. \overline{CE}_0 and \overline{OE} = V_{IL}; CE₁, R/ \overline{W} , and \overline{CNTRST} = V_{IH}.
- 2. If there is no address change via ADS = VIL (loading a new address) or CNTEN = VIL (advancing the address), i.e. ADS = VIH and CNTEN = VIH, then the data output remains constant for subsequent clocks.

3753 drw 17

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)(2)



- 1. $\overline{CE_0}$ and R/W = VIL; CE1 and \overline{CNTRST} = VIH.
- 2. $\overline{CE}_0 = V_{IL}$; CE1 = V_{IH}.
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset. ADDRo will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance.
 The 'An +1'Address is written to during this cycle.

Functional Description

The IDT70V9079 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

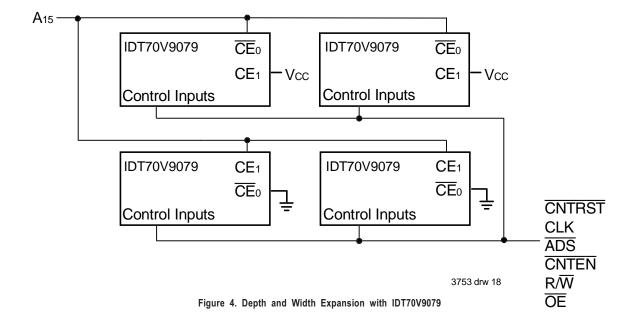
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the counter registers for fast interleaved memory applications.

A HIGH on $\overline{\text{CE}}_0$ or a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V9079's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{\text{CE}}_0$ LOW and CE1 HIGH to re-activate the outputs.

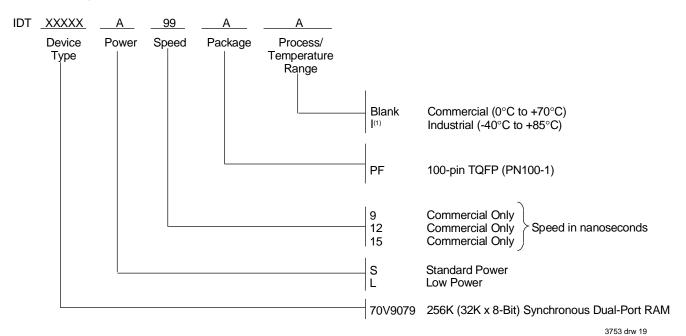
Depth and Width Expansion

The IDT70V9079 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The 70V9079 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 16-bit or wider applications.



Ordering Information



NOTE:

Industrial temperature range is available.
 For specific speeds, packages and powers contact your sales office.

Preliminary Datasheet: Definition

"PRELIMINARY" datasheets contain descriptions for products that are in early release.

Datasheet Document History

1/12/99: Initiated datasheet document history

Converted to new format

Cosmetic and typographical corrections Added additional notes to pin configurations

Page 14 Added Depth and Width Expansion section

6/11/99: Page 3 Deleted note 6 for Table II



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